

## 2SK508

### N-CHANNEL JFET

## HIGH FREQUENCY AMPLIFIER N-CHANNEL SILICON JUNCTION FIELD EFFECT TRANSISTOR

### DESCRIPTION

The UTC **2SK508** is NPN transistor with High forward transfer admittance and low input capacitance.

It is suitable for cordless telephone, AM tuner and wireless installation, etc.

#### FEATURES

\* High forward transfer admittance

\* Low input capacitance

#### ORDERING INFORMATION

Ordering Number		Packago	Pin Assignment			Packing	
Lead Free	Halogen Free	Fackage	1	2	3	Facking	
2SK508L-xxx-AE3-R	2SK508G-xxx-AE3-R	SOT-23	S	D	G	Tape Reel	
Note: Pin Assignment: S: Source D: Drain G: Gate							
2SK508 <u>G-xxx-AE3-R</u> (1)Packing Type (2)Package Type (3)Rank (4)Green Package		<ul> <li>(1) R: Tape Reel</li> <li>(2) AE3: SOT-23</li> <li>(3) x: Refer to Classification of I<sub>DSS</sub></li> <li>(4) G: Halogen Free and Lead Free, L: Lead Free</li> </ul>					

#### MARKING





#### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Gate to Drain Voltage	V <sub>GDO</sub>	-15	V
Gate to Source Voltage	V <sub>GSO</sub>	-15	V
Drain to Source Voltage (V <sub>GS</sub> =-4.0 V)	V <sub>DSX</sub>	15	V
Drain Current (DC)	I <sub>D</sub>	50	mA
Gate Current (DC)	l <sub>G</sub>	5	mA
Power Dissipation	PD	200	mW
Junction Temperature	TJ	+150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Gate Cut-Off Current	I <sub>GSS</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =0V			-1.0	nA
Zero Gate Voltage Drain Current (Note)	I <sub>DSS</sub>	V <sub>DS</sub> =5.0V, V <sub>GS</sub> =0V	10	20	50	mA
Gate to Source Cut-Off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =5.0V, I <sub>D</sub> =10µA	-0.6	-1.4	-3.5	V
Converd Transfer Admittance (Note)	y <sub>FS</sub>  1	V <sub>DS</sub> =5.0V, I <sub>D</sub> =10mA, f=1.0kHz	14	19		mS
Forward Transfer Admittance (Note)	y <sub>FS</sub> 2	V <sub>DS</sub> =5.0V, V <sub>GS</sub> =0V, f=1.0kHz	14	26		mS
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =5.0V, I <sub>D</sub> =10mA, f=1.0MHz		4.8		pF
Feedback Capacitance	C <sub>RSS</sub>	V <sub>DS</sub> =5.0V, I <sub>D</sub> =10mA, f=1.0MHz		1.6		pF

Note: Pulsed:  $P_W \le 1ms$ , Duty Cycle  $\le 1\%$ .

#### ■ I<sub>DSS</sub> CLASSIFICATION

MARKING	K51	K52	K53
I <sub>DSS</sub> (mA)	10 ~ 20	15 ~ 30	25 ~ 50



# 2SK508

### TYPICAL CHARACTERISTICS





Power Dissipation vs. Ambient Temperature



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